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2N6557
2N6558
2N6559
NPN SILICON HIGH VOLTAGE TRANSISTOR

TO-202

MAXIMUM RATINGS (T_A=25°C unless otherwsie noted)

	SYMBOL	2N6557	2N6558	2N6559	UNIT
Collector-Base Voltage	V_{CBO}	250	300	350	V
Collector Emitter Voltage	V_{CEO}	250	300	350	V
Emitter Base Voltage	V_{EBO}		6.0		V
Collector Current	I_C		0.5		A
Collector Current(PEAK)	I_{CM}		0.7		A
Base Current	I_B		250		mA
Power Dissipation	P_D		2.0		W
Power Dissipation(T_C=25°C)	P_D		10		W
Operating and Storage Junction Temperature	T_J,T_{stg}		-65 TO +150		°C
Thermal Resistance	θJA		62.5		°C/W
Thermal Resistance	θJC		12.5		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

			2N6557		2N6558		2N6559		
			MIN	MAX	MIN	MAX	MIN	MAX	UNIT
I_{CBO}	V_{CB}=150V			0.2		-		-	μA
I_{CBO}	V_{CB}=200V			-		0.2		-	μA
I_{CBO}	V_{CB}=250V			-		-		0.2	μA
I_{EBO}	V_{BE}=5.0			0.1		0.1		0.1	μA
BV_{CBO}	I_C=100μA		250		300		350		V
BV_{CEO}	I_C=1.0mA		250		300		350		V
BV_{EBO}	I_E=100μA		6.0		6.0		6.0		V
$V_{CE(SAT)}$	I_C=30mA,	I_B=3.0mA		0.6		0.6		0.6	V
$V_{CE(SAT)}$	I_C=50mA,	I_B=5.0mA		1.5		1.5		1.5	V
$V_{BE(ON)}$	V_{CE}=10V,	I_C=30mA		0.85		0.85		0.85	V
h_{FE}	V_{CE}=10V,	I_C=1.0mA	25		25		25		
h_{FE}	V_{CE}=10V,	I_C=30mA	40	180	40	180	40	180	
f_T	V_{CE}=20V,	I_C=10mA, f=20MHz	45	200	45	200	45	200	MHz
C_{ob}	V_{CB}=20V,	I_E=0, f=1.0MHz		3.0		3.0		3.0	pF